

# LITERATURE REVIEW

SL. NO	TITLE	YEAR	TECHNOLOGY	DRAWBACKS	LIN K
01	Advancing cryptographic security: a novel hybrid AES-RSA model with byte-level tokenization	Apr 16, 2024	<ul style="list-style-type: none"><li>• byte-level Byte-Pair Encoding (BPE) tokenizer.</li><li>• RSA algorithm</li><li>• Advanced Encryption Standard (AES).</li></ul>	<ul style="list-style-type: none"><li>• Increased Computational Overhead</li><li>• Complexity in Key Management</li><li>• Potential Vulnerabilities in Tokenization</li></ul>	<a href="#">[A]</a>
02	Design and Implementation of Memory Controller for Byte Access from Data Memory for SoC's Devices	July, 2024	<ul style="list-style-type: none"><li>• System-on-Chip (SoC) Architecture.</li><li>• Advanced eXtensible Interface (AXI).</li><li>• Verilog and SystemVerilog UVM (Universal Verification Methodology).</li></ul>	<ul style="list-style-type: none"><li>• Limited Scalability in Multi-Processor Environments.</li><li>• Limited Flexibility in Dynamic Environments</li><li>• Verification and Validation Challenges</li></ul>	<a href="#">[B]</a>
03	Optimizing Systems for Byte-Addressable NVM by Reducing Bit Flipping	February, 2019	<ul style="list-style-type: none"><li>• Phase Change Memory (PCM).</li><li>• XOR Linked Lists.</li><li>• XOR Hash Tables.</li><li>• XOR Red-Black Tree.</li></ul>	<ul style="list-style-type: none"><li>• PCM Write Endurance Power Consumption</li><li>• Memory Allocation Overhead.</li><li>• XOR Hash Tables, Complexity</li></ul>	<a href="#">[C]</a>

<b>04</b>	<b>20nm High-density single-port and dual-port SRAMa with worldline-voltage-adjustments system for read/write assists</b>	<b>06 March 2014</b>	<ul style="list-style-type: none"><li>• <b>Wordline-Voltage-Adjustment System</b></li><li>• <b>On-Chip Voltage Regulator</b></li><li>• <b>Temperature Monitoring and Control</b></li><li>• <b>Temperature and Process Variation-Based Adjustmen</b></li></ul>	<ul style="list-style-type: none"><li>• <b>Increased Complexity</b></li><li>• <b>Write/Read Disturb Issues in DP-SRAM</b></li><li>• <b>Timing Considerations</b></li></ul>	<a href="#"><u>[D]</u></a>
<b>05</b>	<b>A 45-nm Single-port and Dual-port SRAM family with Robust Read/Write Stabilizing Circuitry under DVFS Environment.</b>	<b>01 August 2008</b>	<ul style="list-style-type: none"><li>• <b>Improved Wordline Suppression Circuitry</b></li><li>• <b>Negative Bitline Technique.</b></li><li>• <b>45nm CMOS Technology</b></li></ul>	<ul style="list-style-type: none"><li>• <b>Process Variation Sensitivity</b></li><li>• <b>Complexity in Negative Bitline Implementation</b></li></ul>	<a href="#"><u>[E]</u></a>